
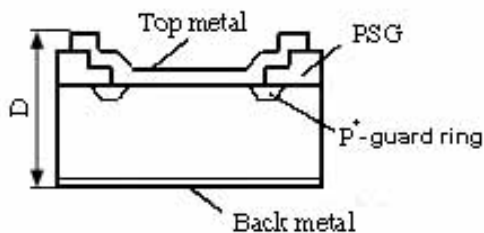
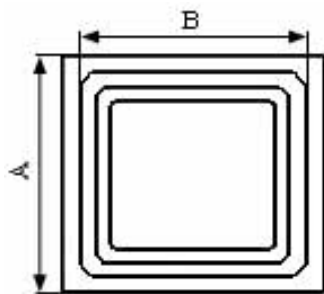


**SCHOTTKY DIODES KDN-15020.**  
**PRELIMINARY**



Rev.1. Feb. 2010

 <b>VSP-MIKRON</b>	<b>15A/20V. Die Size-106mil.</b>			
<b>Electrical Characteristics</b>	<b>Symbol</b>	<b>Unit</b>	<b>Spec. limit</b>	<b>Die Sort</b>
Breakdown Voltage @ $I_R=10mA$	$V_{BR}$	V	20	25
Average Rectified Forward Current	$I_{F(AV)}$	A	15,0	-
DC Forward Voltage @ $25^{\circ}C, I_F=15,0A$	$V_F$	V	0,50	0,48
Maximum Reverse Current @ $25^{\circ}C, V_R=25V$ @ $25^{\circ}C, V_R=20V$ @ $125^{\circ}C, V_R=20V$	$I_R$	mA	- 0,350 200,0	0,350 0,300 180,0
Peak Forward Surge Current 8,3ms single half sine-wave superimposed on rated load (JEDEC METHOD)	$I_{FSM}$	A	180	-
Peak Repetitive Reverse Surge Current @ $2,0\mu s, f=1kHz., T_J<150^{\circ}C.$	$I_{RRM}$	A	4,0	
Electrostatic Discharge Voltage. JEDEC Method. ESD HBM. Contact.	ESD	kV	$\pm 8$ (contact)	
Voltage Rate of Change	dV/dt	V/ $\mu S$	10.000	
Operating Junction Temperature	$T_J$	$^{\circ}C$	150	



<b>DIM</b>	<b>ITEM</b>	<b><math>\mu m</math></b>
$A_x$ $A_y$	Wafer Form Die Size	2700 2700
$B_x$ $B_y$	Top Metal Size	2560 2560
D	Thickness	350max.
Scribe line Width		80

*Top metal:* a) **Al** – for Wire Bonding;  
b) **Al-Ni-Ag**; - for Soldering.  
*Backside metal:* **Ti-Ni-Ag**.